

Low signal distortion, surface mount RF PIN diode, series pair









Product description

This Infineon cost optimized RF PIN diode is designed for low distortion switches that require to hold off large RF voltages, and is best suited for frequencies as high as 3 GHz. Its nominal 50 μ m I-region width, combined with the typical 1.55 μ s carrier lifetime, result in a diode with low forward resistance and low distortion characteristics.



Feature list

- Low signal distortion, charge carrier lifetime t_{rr} = 1.55 µs (typical)
- Very low capacitance C = 0.22 pF (typical) at voltage $V_R = 0$ and frequencies $f \ge 1$ Ghz
- Low forward resistance $R_F = 2.3 \Omega$ (typical) at forward current $I_F = 10 \text{ mA}$ and frequency f = 100 MHz
- Industry standard SOT23-3 package (2.9 mm x 2.4 mm x 1 mm)
- Pb-free, RoHS compliant and halogen-free

Product validation

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22.

Potential applications

Optimized for low bias current RF and high-speed interface switches and attenuators

- Wireless communication
- High speed data networks

Device information

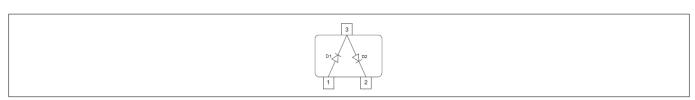


Table 1 Part i	information
----------------	-------------

Product name / Ordering code	Package	Pin configuration	Marking	Pieces / Reel
BAR64-04 / BAR6404E6327HTSA1	SOT23-3	Series pair	PPs	3 k

Attention: ESD (Electrostatic discharge) sensitive device, observe handling precautions!

Low signal distortion, surface mount RF PIN diode, series pair



Table of contents

Table of contents

	Product description	
	Feature list	1
	Product validation	1
	Potential applications	
	Device information	
	Table of contents	2
1	Absolute maximum ratings	2
2	Electrical performance in test fixture	3
2.1	DC characteristics	
2.2	AC characteristics	
3	Thermal characteristics	9
4	Package information SOT23-3	11
	Revision history	12
	Disclaimer	13

1 Absolute maximum ratings

Table 2 Absolute maximum ratings at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Va	lues	Unit	Note or test condition
		Min.	Max.		
Diode reverse voltage	V_{R}	_	150	V	
Forward current	/ _F	_	100	mA	
Total power dissipation	P_{TOT}	_	250	mW	T _S ≤ 126 °C ¹⁾
Junction temperature	T _J	_	150	°C	
Operating temperature	T_{OP}	-55	125		
Storage temperature	T_{STG}	-55	150		

Attention: Stresses above the maximum values listed here may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Exceeding only one of these values may cause irreversible damage to the component.

 $T_{\rm S}$ is the soldering point temperature.



Electrical performance in test fixture

2 Electrical performance in test fixture

2.1 DC characteristics

At T_A = 25 °C, unless otherwise specified

Table 3 DC characteristics

Parameter	Symbol		Values	i	Unit	Note or test condition
		Min.	Тур.	Мах.		
Breakdown voltage	V_{BR}	150	_	_	V	$I_R = 5 \mu A$
Reverse current	I_{R}	-	_	20	nA	V _R = 20 V
Forward voltage	V_{F}	_	0.82	_	٧	/ _F = 10 mA
		_	0.9	_		I _F = 50 mA
		_	0.95	1.1		/ _F = 100 mA
I-region width	W_1	_	50	_	μm	

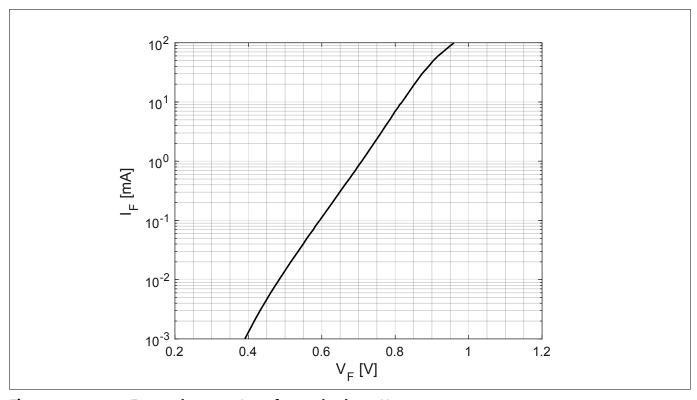


Figure 1 Forward current I_F vs. forward voltage V_F

Low signal distortion, surface mount RF PIN diode, series pair



Electrical performance in test fixture

2.2 AC characteristics

At T_A = 25 °C, unless otherwise specified

Table 4 Key parameter

Parameter	Symbol		Values	i	Unit	Note or test condition
		Min.	Тур.	Max.		
Capacitance	С	_	0.6	_	pF	$V_{R} = 0 \text{ V}, f = 1 \text{ MHz}$
		_	0.23	0.35		V _R = 20 V, f = 1 MHz
Forward resistance	R_{F}	_	10.7	20		$I_{\rm F}$ = 1 mA, f = 100 MHz
		_	4.6	_		$I_{\rm F}$ = 3 mA, f = 100 MHz
		_	3.3	_		$I_{\rm F}$ = 5 mA, f = 100 MHz
		_	2.3	2.8		I _F = 10 mA, f = 100 MHz
		_	_	1.35		$I_{\rm F}$ = 100 mA, f = 100 MHz
Inductance	L _s	_	1.8	-	nH	
Charge carrier lifetime	$ au_{rr}$	_	1550	-	ns	$I_F = 10 \text{ mA}, I_R = 6 \text{ mA},$ measured at $I_R = 3 \text{ mA},$ $R_L = 100 \Omega$

Table 5 AC parameter f = 1 GHz

Parameter	Symbol		Values	;	Unit	Note or test condition
		Min.	Тур.	Max.		
Capacitance	С	_	0.22	_	pF	<i>V</i> _R = 0 V
Reverse parallel resistance	R _P	_	3.5	_	kΩ	V _R = 0 V
Forward resistance	R _F	_	10.4	_	Ω	/ _F = 1 mA
		_	4.7	_		I _F = 3 mA
		_	3.5	_		I _F = 5 mA
		_	2.5	_		/ _F = 10 mA
Insertion loss	/L	_	0.87	_	dB	/ _F = 1 mA
		_	0.42	_		I _F = 3 mA
		_	0.32	_		I _F = 5 mA
		_	0.24	_		/ _F = 10 mA
Isolation	I _{SO}	_	17.5	_		<i>V</i> _R = 0 V

Table 6 AC parameter at f = 1.8 GHz

Parameter	Symbol	Values			Values Unit		Unit	Note or test condition
		Min.	Тур.	Max.				
Capacitance	С	_	0.22	-	pF	V _R = 0 V		
Reverse parallel resistance	R _P	_	2.8	_	kΩ	V _R = 0 V		

Low signal distortion, surface mount RF PIN diode, series pair



Electrical performance in test fixture

Table 6 AC parameter at f = 1.8 GHz (continued)

Parameter	Symbol		Values	•	Unit	Note or test condition
		Min.	Тур.	Max.		
Forward resistance	R _F	_	10.5	_	Ω	/ _F = 1 mA
		_	4.8	_		I _F = 3 mA
		_	3.6	_		I _F = 5 mA
		_	2.6	_		/ _F = 10 mA
Insertion loss	I _L	_	0.92	_	dB	/ _F = 1 mA
		_	0.48	_		$I_{\rm F}$ = 3 mA
		_	0.38	_		I _F = 5 mA
		_	0.3	_		/ _F = 10 mA
Isolation	I _{SO}	_	12.8	-		<i>V</i> _R = 0 V

Table 7 AC parameter at f = 2.5 GHz

Parameter	Symbol		Values	;	Unit	Note or test condition
		Min.	Тур.	Max.		
Capacitance	С	_	0.22	_	pF	V _R = 0 V
Reverse parallel resistance	R_{P}	_	2.5	_	kΩ	V _R = 0 V
Forward resistance	R_{F}	_	10.8	_	Ω	/ _F = 1 mA
		_	5	_		I _F = 3 mA
		_	3.8	_		I _F = 5 mA
		_	2.8	_		/ _F = 10 mA
Insertion loss	I _L	_	0.99	_	dB	/ _F = 1 mA
		_	0.56	_		I _F = 3 mA
		_	0.46	_		I _F = 5 mA
		_	0.35	_		/ _F = 10 mA
Isolation	I _{SO}	_	10.4	_		V _R = 0 V



Electrical performance in test fixture

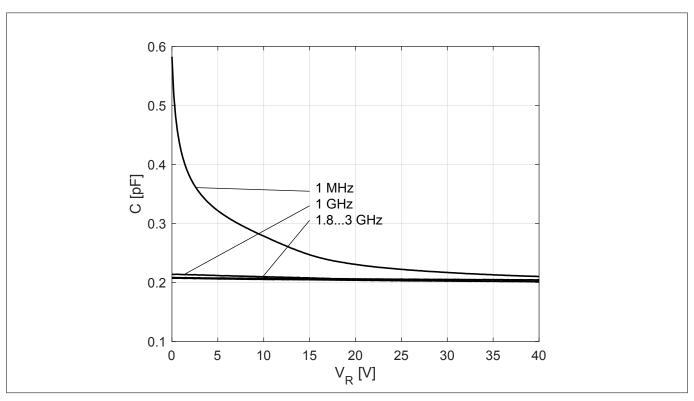


Figure 2 Capacitance C vs. reverse voltage V_R at different frequencies

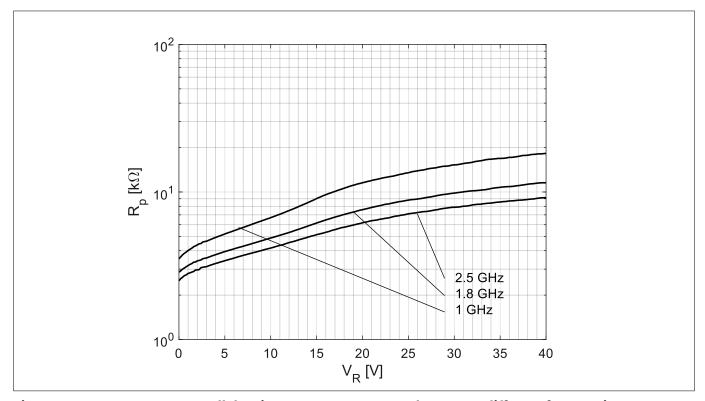


Figure 3 Reverse parallel resistance R_P vs. reverse voltage V_R at different frequencies



Electrical performance in test fixture

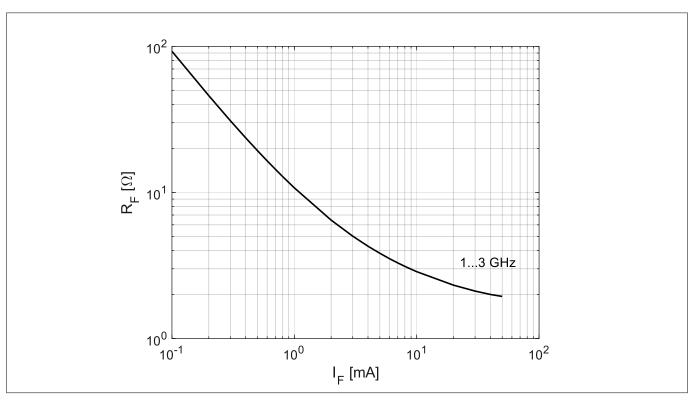


Figure 4 Forward resistance R_F vs. forward current I_F at different frequencies

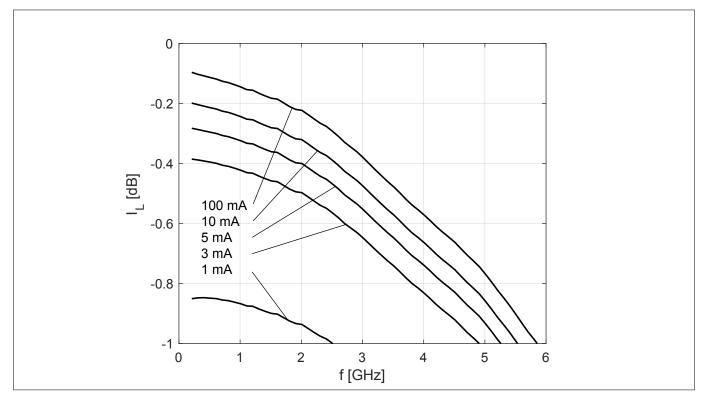


Figure 5 Insertion loss I_L vs. frequency f at different forward currents

Low signal distortion, surface mount RF PIN diode, series pair



Electrical performance in test fixture

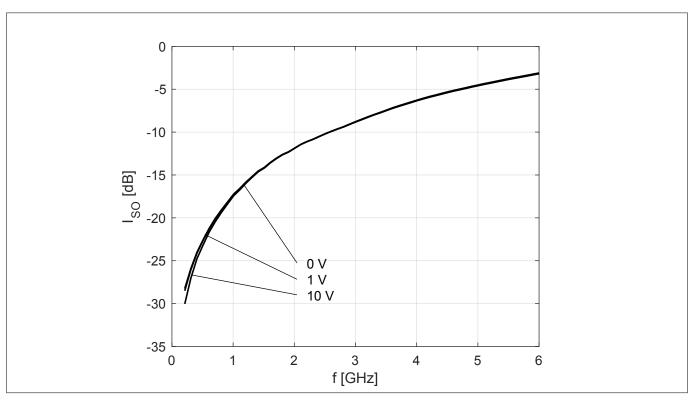


Figure 6 Isolation I_{SO} vs. frequency f at different reverse voltages

Note: The curves shown in this chapter have been generated using typical devices but shall not be understood as a guarantee that all devices have identical characteristic curves.



Thermal characteristics

3 Thermal characteristics

Table 8 Thermal resistance

Parameter	Sym bol	Values			Unit	Note or test condition	
		Min.	Тур. Мах.				
Thermal resistance	R _{thJS}	_	95	_	K/W	T _S = 126 °C ²⁾	
(junction - soldering point)							

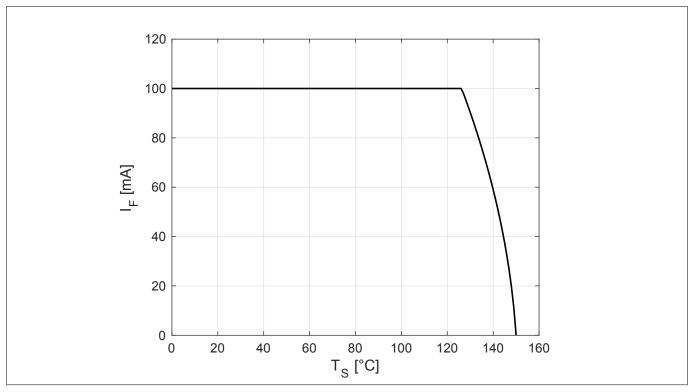


Figure 7 Permissible forward current I_F in DC operation

² For R_{thJS} in other conditions refer to the curves in this chapter.



Thermal characteristics

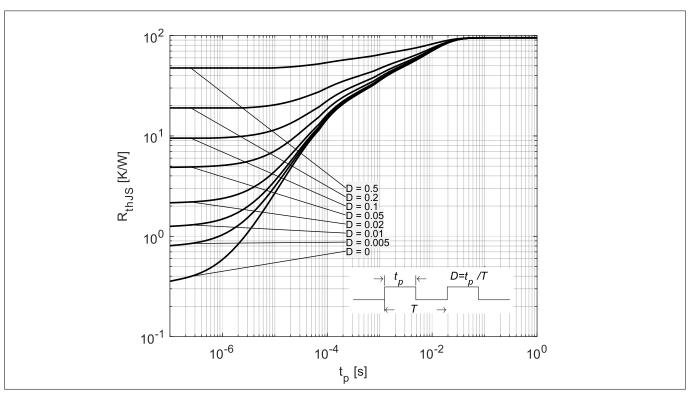


Figure 8 Thermal resistance R_{thJS} in pulse operation

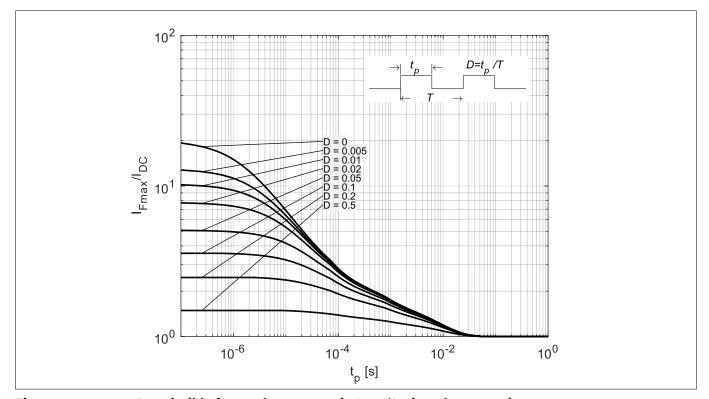


Figure 9 Permissible forward current ratio I_{Fmax}/I_{DC} in pulse operation

10



Package information SOT23-3

4 Package information SOT23-3

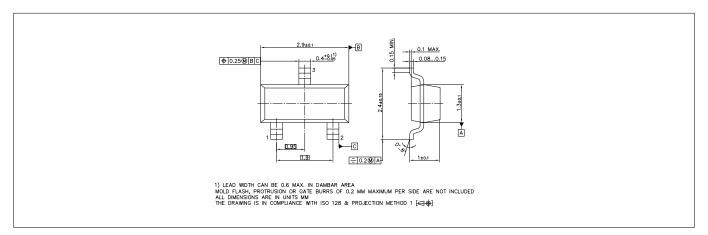


Figure 10 Package outline

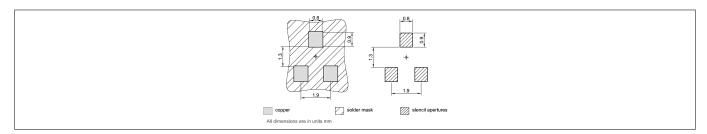


Figure 11 Foot print

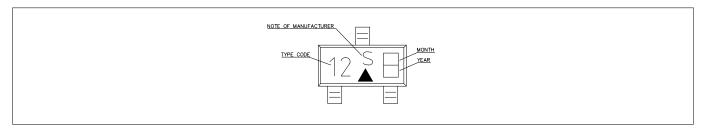


Figure 12 Marking layout example

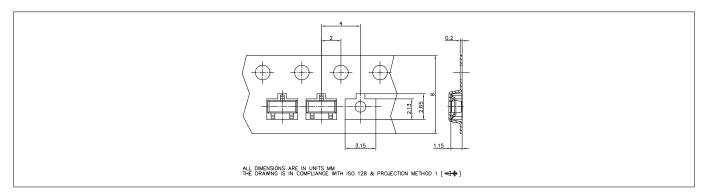


Figure 13 Tape dimensions

Low signal distortion, surface mount RF PIN diode, series pair



Revision history

Revision history

Document version	Date of release	Description of changes
1.0	2018-09-07	 Change from series datasheet to individual one Initial release of datasheet Typical values and curves updated to the values of the production (No product or process change behind) Maximum/typical values added Typical curves/values removed
1.1	2019-01-21	Product description, feature list and potential application section reworked

Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

Edition 2018-06-30 Published by Infineon Technologies AG 81726 Munich, Germany

© 2019 Infineon Technologies AG All Rights Reserved.

Do you have a question about any aspect of this document?

 ${\bf Email: erratum@infineon.com}$

Document reference IFX-xtp1535447359276

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for PIN Diodes category:

Click to view products by Infineon manufacturer:

Other Similar products are found below:

MA45471 MA4SPS502 APD2220-000 APD0810-000 MA4GP907 MA4L032-186 MA4L401-30 MA4P606-258 MA4P7435NM-1091T

MA4PK2000 MA4PK2001 MA4PK2004 MADP-007167-12250T MADP-030025-13140P MA4SPS421 MA4PBL027 MA4P404-30

MA4AGFCP910 MA4P7101F-1072T MA4L022-30 MA47047-54 BAR 89-02LRH E6327 UM7108B UM9701 1SV308,L3F UM9301SM

5082-3077 GC4723-42 MA4L011-1088 MSW2001-200 SMP1321-000 M17X1008 UM4010SM UM6002B UM7201SM UM7006A

UM7006B UM7108C GC4742-42 MADP-000015-000030 MGPN1503-C01A UMX512 LXP1000-23-2 LXP1004-23-2 MPP4205A-206

MPP4201-206 LXP1002-23-0 LXP1004-23-0 MPP4202-206 MPP4205-206